



RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for GSM and GSM EDGE base station applications with frequencies from 1800 to 2000 MHz. Suitable for FM, TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for GSM and GSM EDGE cellular radio applications.

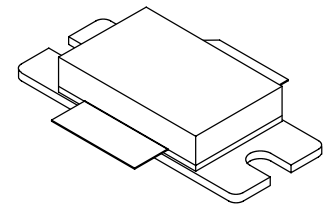
- GSM and GSM EDGE Performances @ 1805 MHz
 Power Gain — 13.5 dB (Typ) @ 90 Watts CW
 Efficiency — 52% (Typ) @ 90 Watts CW
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 90 Watts CW Output Power

Features

- Internally Matched for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF18090AR3

**1805-1880 MHz, 90 W, 26 V
 LATERAL N-CHANNEL
 RF POWER MOSFET**



**CASE 465B-03, STYLE 1
 NI-880**

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Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	250 1.43	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

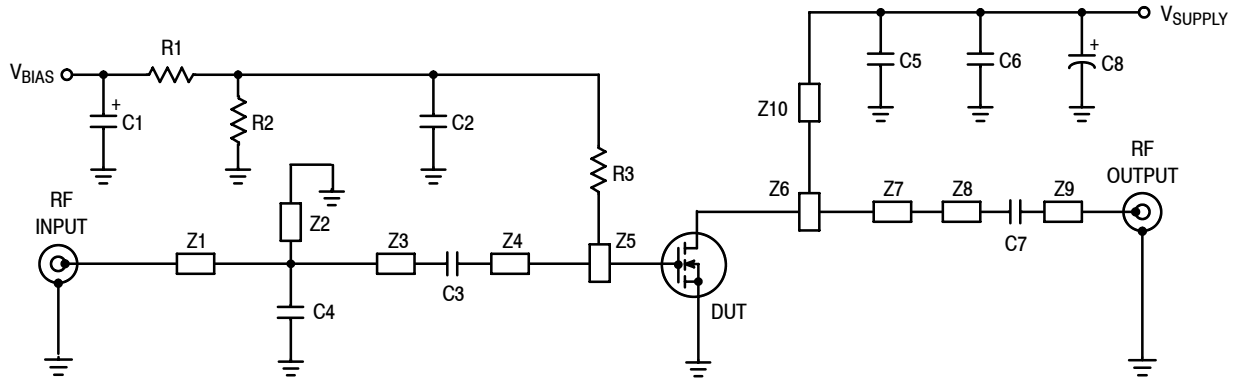
Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	$^\circ\text{C}/\text{W}$

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	2 (Minimum)
Machine Model	M3 (Minimum)

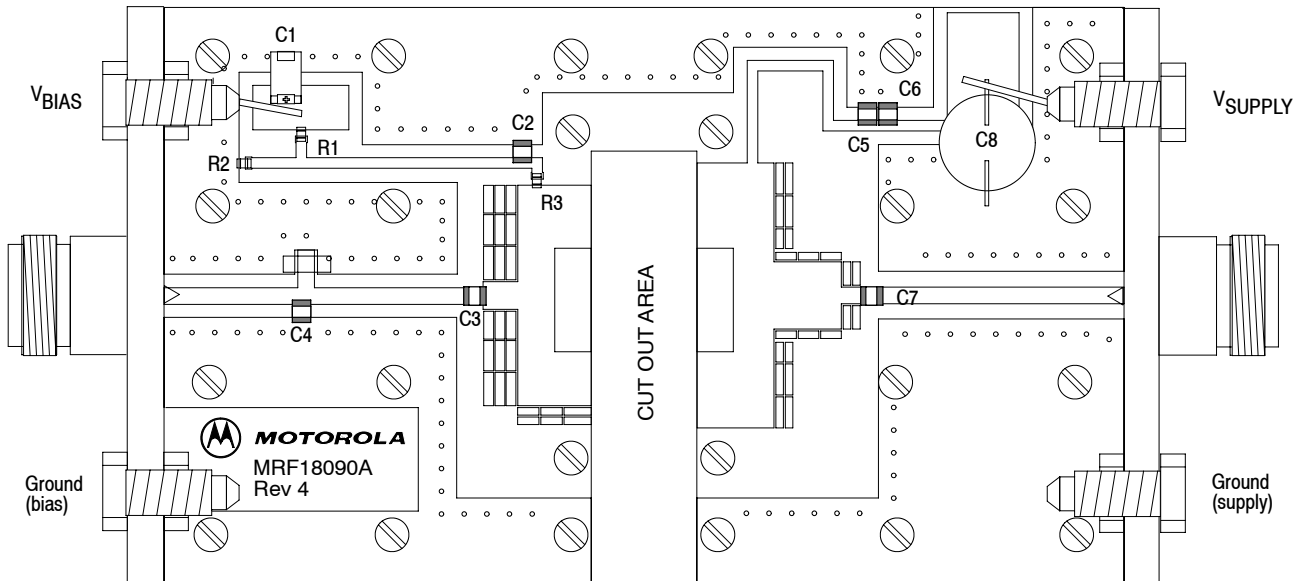
Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 100\ \mu\text{Adc}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 750\text{ mAdc}$)	$V_{GS(Q)}$	2.5	3.7	4.5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1\text{ Adc}$)	$V_{DS(on)}$	—	0.1	—	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	g_{fs}	—	7.2	—	S
Dynamic Characteristics					
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	4.2	—	pF
Functional Tests (In Freescale Test Fixture)					
Common-Source Amplifier Power Gain @ 90 W ($V_{DD} = 26\text{ Vdc}$, $I_{DQ} = 750\text{ mA}$, $f = 1805\text{ MHz}$)	G_{ps}	12.0	13.5	—	dB
Drain Efficiency @ 90 W ($V_{DD} = 26\text{ Vdc}$, $I_{DQ} = 750\text{ mA}$, $f = 1805\text{ MHz}$)	η	47	52	—	%
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W CW}$, $I_{DQ} = 750\text{ mA}$, $f = 1805\text{ MHz}$)	IRL	—	—	-10	dB



C1	10 μ F, 35 V Tantalum Capacitor	Z3	0.819" x 0.087" Microstrip
C2, C3	10 pF, 100B Chip Capacitors	Z4	0.181" x 0.144" Microstrip
C4	3.3 pF, 100B Chip Capacitor	Z5	0.383" x 1.148" Microstrip
C5, C6	6.8 pF, 100B Chip Capacitors	Z6	0.400" x 1.380" Microstrip
C7	12 pF, 100B Chip Capacitor	Z7	0.351" x 0.351" Microstrip
C8	220 μ F, 63 V Electrolytic Capacitor	Z8	0.126" x 0.087" Microstrip
R1, R2	10 k Ω , 1/8 W Chip Resistors (0805)	Z9	1.280" x 0.087" Microstrip
R3	1.0 k Ω , 1/8 W Chip Resistor (0805)	Z10	\approx 1.275" x 0.055" Microstrip
Z1	0.697" x 0.087" Microstrip	PCB	Taconic TLX8-0300, 0.030", $\epsilon_r = 2.55$
Z2	0.087" x 0.197" Microstrip		

Figure 1. MRF18090A 1805 - 1880 MHz Test Fixture Schematic



Freescall has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescall Semiconductor signature/logo. PCBs may have either Motorola or Freescall markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF18090A 1805 - 1880 MHz Test Fixture Component Layout

TYPICAL CHARACTERISTICS

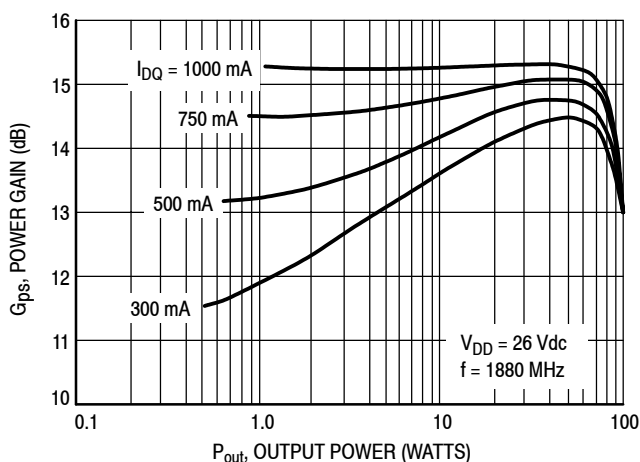


Figure 5. Power Gain versus Output Power

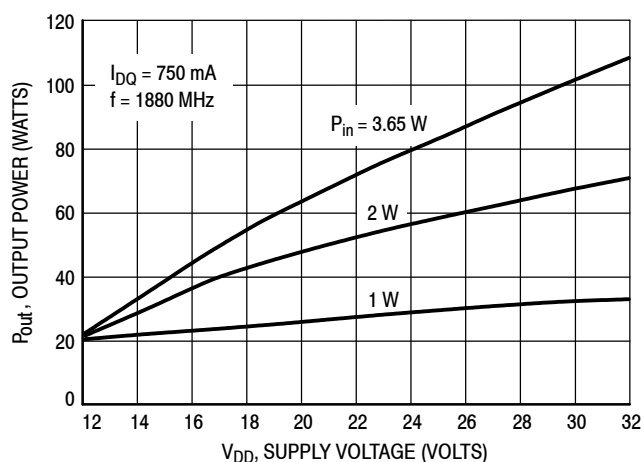


Figure 6. Output Power versus Supply Voltage

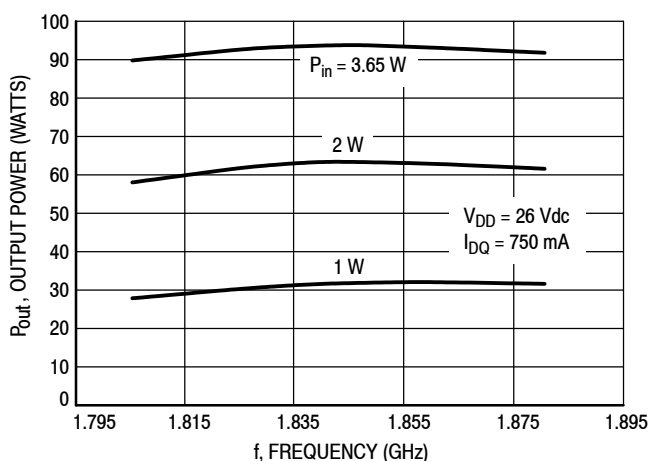


Figure 7. Output Power versus Frequency

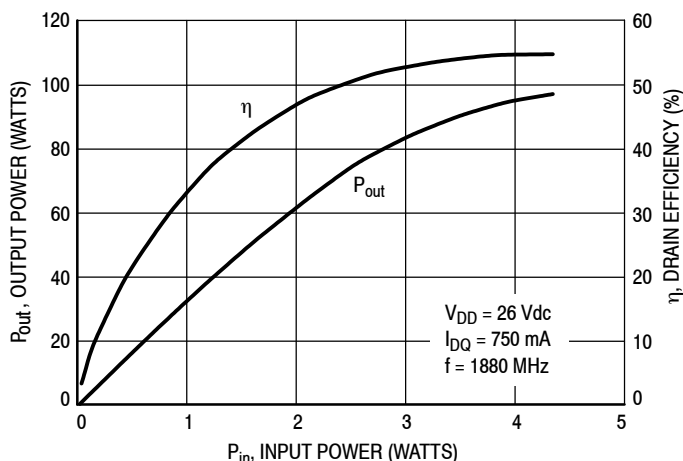


Figure 8. Output Power and Efficiency versus Input Power

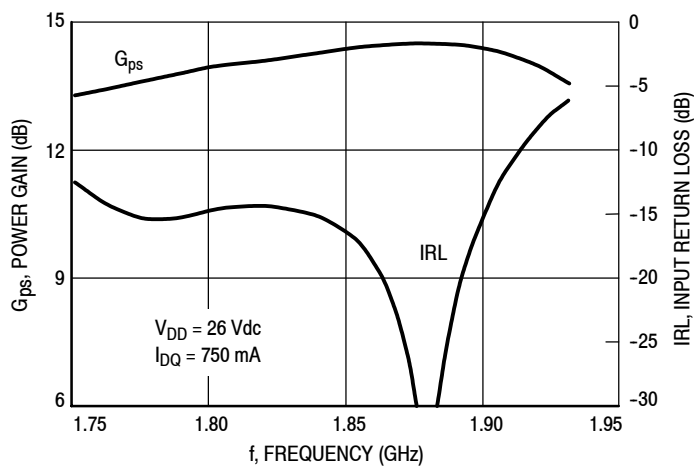
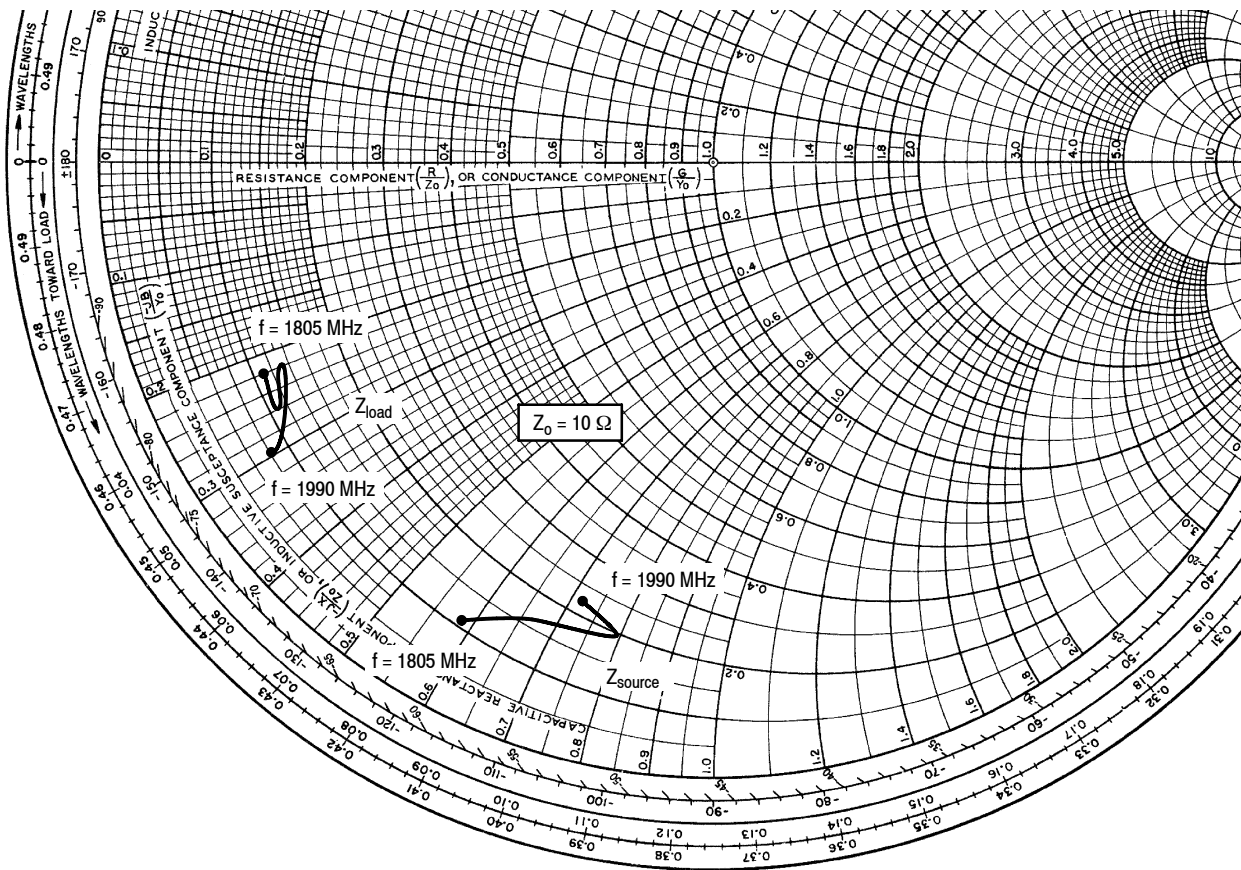


Figure 9. Wideband Gain and IRL (at Small Signal)

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$V_{DD} = 26\text{ V}$, $I_{DQ} = 750\text{ mA}$, $P_{out} = 90\text{ Watts (CW)}$

f MHz	Z_{source} Ω	Z_{load} Ω
1805	$1.10 - j5.85$	$1.15 - j2.16$
1880	$1.56 - j6.75$	$1.13 - j2.60$
1930	$2.05 - j8.00$	$1.30 - j2.23$
1990	$2.30 - j7.30$	$0.82 - j2.90$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

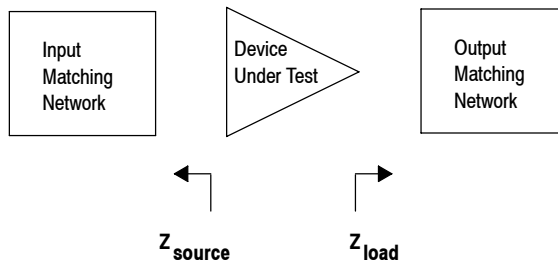
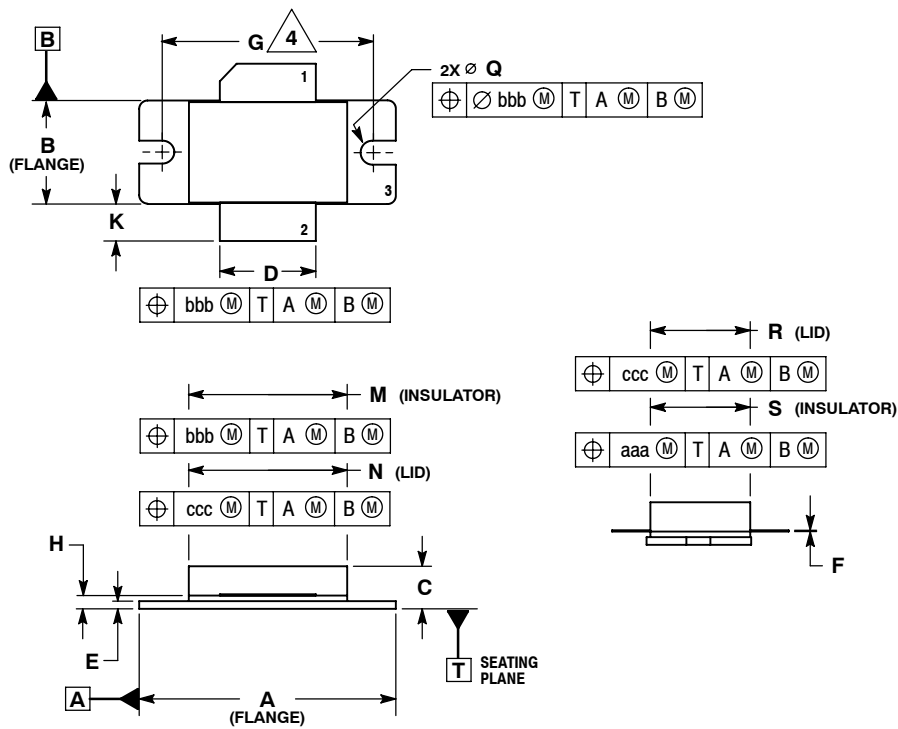


Figure 10. Large Signal Source and Load Impedance

PACKAGE DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
4. RECOMMENDED BOLT CENTER DIMENSION OF 1.16 (29.57) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.175	0.205	4.44	5.21
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	\varnothing 1.118	\varnothing 1.138	\varnothing 3.00	\varnothing 3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:

- PIN 1. DRAIN
- 2. GATE
- 3. SOURCE

**CASE 465B-03
ISSUE D
NI-880**

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PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
8	Oct. 2008	<ul style="list-style-type: none">• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 1, 2• Added Product Documentation and Revision History, p. 8
	Dec. 2010	<ul style="list-style-type: none">• Data sheet archived. Part no longer manufactured.

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